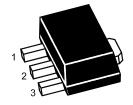


## **PNP Silicon Epitaxial Power Transistor**

- Darlington Transistor
- for high gain amplification



1.Base 2.Collector 3.Emitter SOT-89 Plastic Package

## Absolute Maximum Ratings ( $T_a = 25$ °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	-V <sub>CBO</sub>	100	V
Collector Emitter Voltage	-V <sub>CEO</sub>	100	V
Emitter Base Voltage	-V <sub>EBO</sub>	10	V
Collector Current (DC) Collector Current (Pulse)	-I <sub>C</sub>	2 3 <sup>1)</sup>	А
Total Power Dissipation	P <sub>tot</sub>	0.5 1 <sup>2)</sup>	W
Junction Temperature	T <sub>j</sub>	125	°C
Storage Junction Temperature Range	T <sub>stg</sub>	- 55 to + 150	°C

<sup>1)</sup> Single pulse: P<sub>W</sub> = 100 ms

## Characteristics at $T_a = 25$ °C

Parameter	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain at -V <sub>CE</sub> = 2 V, -I <sub>C</sub> = 1 A	h <sub>FE</sub>	1000	-	10000	-
Collector Base Cutoff Current at -V <sub>CB</sub> = 100 V	-I <sub>CBO</sub>	-	ı	10	μΑ
Emitter Base Cutoff Current at -V <sub>EB</sub> = 7 V	-I <sub>EBO</sub>	-	1	3	mA
Collector Base Breakdown Voltage at $-I_C = 50 \mu A$	-V <sub>(BR)CBO</sub>	100	1	-	V
Collector Emitter Breakdown Voltage at $-I_C = 5$ mA	-V <sub>(BR)CEO</sub>	100	1	-	V
Emitter Base Breakdown Voltage at $-I_E = 5$ mA	-V <sub>(BR)EBO</sub>	10	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 1 \text{ A}$ , $-I_B = 1 \text{ mA}$	-V <sub>CE(sat)</sub>	-	-	1.5	V
Current Gain Bandwidth Product at -V <sub>CE</sub> = 5 V, $I_E$ = 100 mA, $f$ = 30 MHz	f⊤	-	50	-	MHz
Collector Output Capacitance at -V <sub>CB</sub> = 10 V, f = 1 MHz	C <sub>ob</sub>	-	35	-	pF

 $<sup>^{2)}</sup>$  When mounted on a 250  $\mbox{mm}^2$  x 0.8 t ceramic substrate.

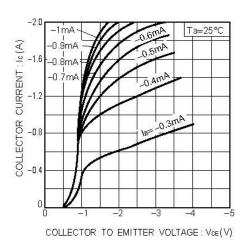


Fig.1 Grounded emitter output characteristics

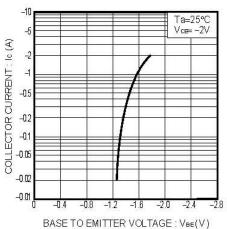


Fig.2 Grounded emitter propagation characteristics

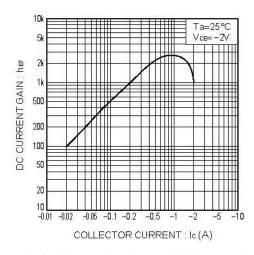


Fig.3 DC current gain vs. collector current

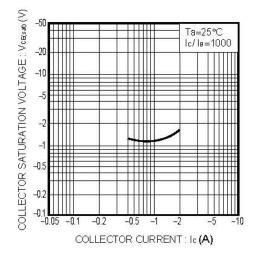
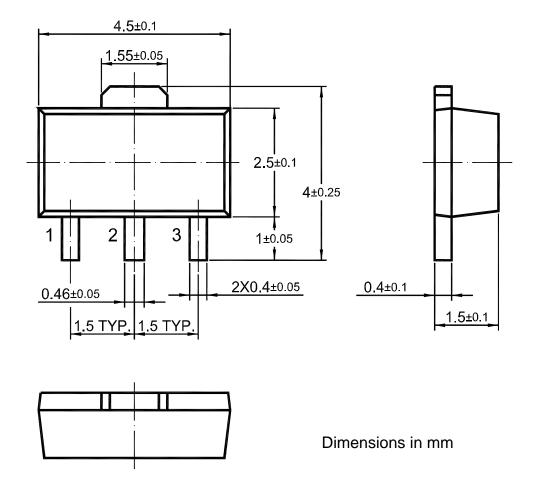


Fig.4 Collector-emitter saturation voltage vs. collector current



## **SOT-89 PACKAGE OUTLINE**



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